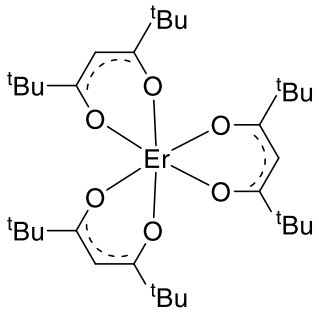
Catalog # 68-8750 Tris(2,2,6,6-tetramethyl-3,5-heptanedionato)erbium(III), 99% (99.9%-Er) (REO)
[Er(TMHD)3]



Thermal Behavior:

- Melting point 179-180°C [1]
- Decomposition 345°C
- Sublimation 160°C/0.1 Torr
- TGA data and diagram is available in [2]
- Vapor Pressure: 0.1 Torr/180°C [4]

Technical Notes:

1. ALD/CVD precursor and dopant for erbium containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Er_2O_3	ALD ALD	130°C 150°C	1.5-2.25 Torr -	O_3 O_2	200-450°C 200-300°C	2-4 5
Er_xY_yO	ALD ALD	- 130°C	- 1.5-3 Torr	O_2 O_3	350°C 300°C	6 7
$Er_xGa_{2-x}O_3$	ALD	130°C	1.5-2.25 Torr	$Ga(acac)_3$, O_3	350°C	8
$Er_xTi_yO_z$	ALD	130°C	-	$TiCl_4$, O_3	300°C	9
$Er_xSc_yO_z$	ALD	130°C	1.5-2.25 Torr	$Sc(thd)_3$, O_3	300°C	10
$Er_xFe_yO_z$	ALD	150°C	11-12 Torr	$Fe(thd)_3$, O_3	275-350°C	11
$Er:Gd_3Ga_5O_{12}$	ALD	200°C	0.5 Torr	O_3, Me_3Ga, $Gd(thd)_3$	350°C	12

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